



150V N-Channel Enhancement Mode MOSFET

Voltage

150 V

Current

25 A

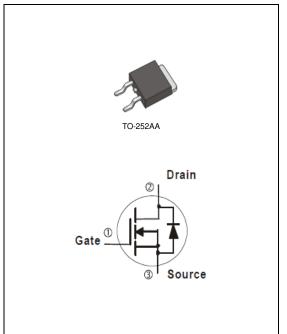
Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_{D}@5A<65m\Omega$
- $R_{DS(ON)}$, $V_{GS}@6V$, $I_D@3A<90m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

• Case : TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMET	ER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	150	V
Gate-Source Voltage		V_{GS}	<u>+</u> 25	V
Cantinua Dunin Comment	T _C =25°C	I _D	25	
Continuous Drain Current	T _C =100°C		16	Α
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	100	
Power Dissipation	T _C =25°C	Po	102	147
	T _C =100°C		41	W
Continuous Drain Current	T _A =25°C	I _D	3.5	А
	T _A =70°C		2.8	А
Power Dissipation	T _A =25°C	5	2.0	147
Power Dissipation	T _A =70°C	Po	1.3	W
Single Pulse Avalanche Energy (Note 6)		E _{AS}	242	mJ
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C
T : T : Note 4.5	Junction to Case	$R_{ heta JC}$	1.23	90044
Typical Thermal Resistance (Note 4,5	Junction to Ambient	$R_{\theta JA}$	62.5	°C/W

[•] Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V,I_D=250uA$	150	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250$ uA	2.0	2.7	4.0	V	
Drain-Source On-State Resistance	D	$V_{GS}=10V,I_{D}=5A$	-	50	65	mΩ	
Dialii-Source Oii-State nesistance	$R_{DS(on)}$	$V_{GS}=6V,I_{D}=3A$	-	60	90		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=150V, V_{GS}=0V$	-	-	1.0	uA	
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 25V, V_{DS} = 0V$	-	-	<u>+</u> 100	nA	
Dynamic (Note 7)							
Total Gate Charge	Q_g	V_{DS} =75V, I_{D} =4A, V_{GS} =10V (Note 1,2)	-	29.5	-	nC	
Gate-Source Charge	Q_gs		-	9.2	-		
Gate-Drain Charge	Q_gd		-	8.0	-		
Input Capacitance	Ciss	V _{DS} =30V, V _{GS} =0V, f=1.0MHZ	-	1764	-	pF	
Output Capacitance	Coss		-	148	-		
Reverse Transfer Capacitance	Crss	I=I.UIVINZ	-	62	-		
Turn-On Delay Time	td _(on)	$V_{DS}{=}30V, I_{D}{=}1A,$ $V_{GS}{=}10V, \ R_{G}{=}6\Omega$ (Note 1,2)	-	14	-	ns	
Turn-On Rise Time	t _r		-	21	-		
Turn-Off Delay Time	td _(off)		-	32	-		
Turn-Off Fall Time	t _f		-	23	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	I.				25	Α	
Diode Forward Current	I _S		-		20	^	
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.7	1.0	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5. R@JA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =22A, V_{DD} =50V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

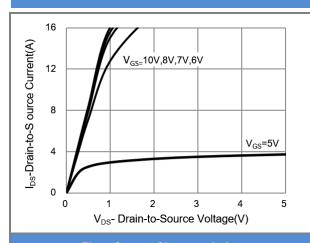


Fig.1 Output Characteristics

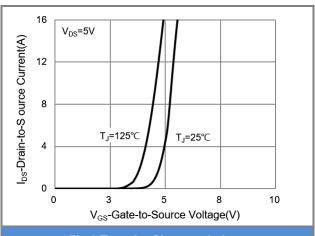


Fig.2 Transfer Characteristics

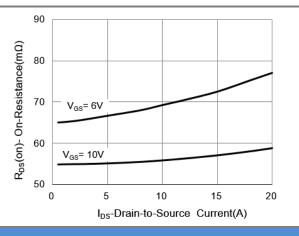


Fig.3 On-Resistance vs. Drain Current

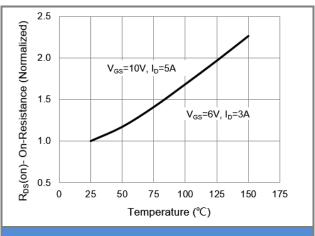


Fig.4 On-Resistance vs. Junction temperature

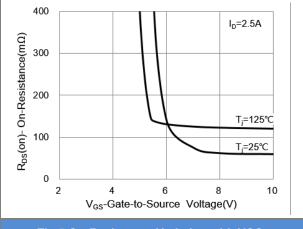


Fig.5 On-Resistance Variation with VGS.

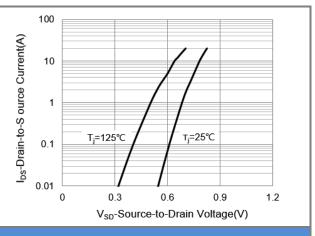


Fig.6 Source-Drain Diode Forward Voltage





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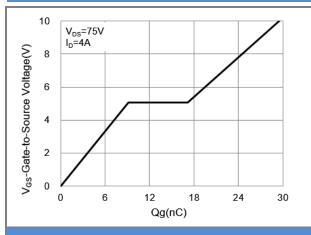


Fig.7 Gate-Charge Characteristics

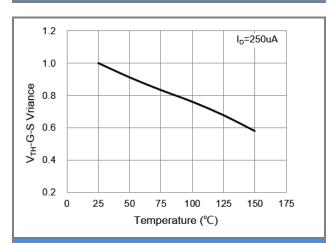
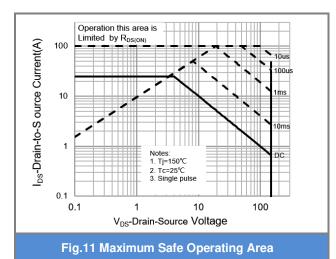


Fig.9 Threshold Voltage Variation with Temperature



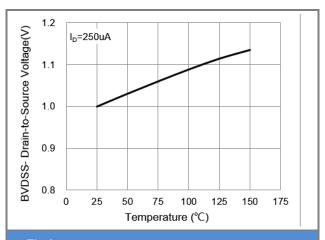


Fig.8 Breakdown Voltage Variation vs. Temperature

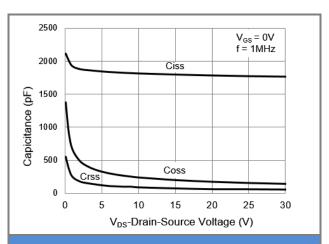


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

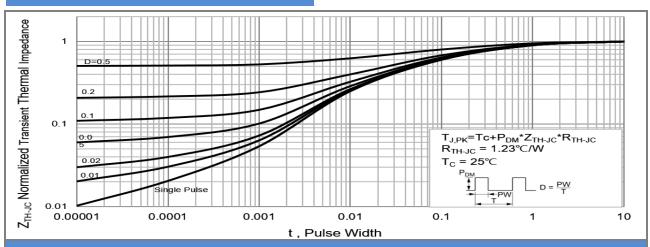
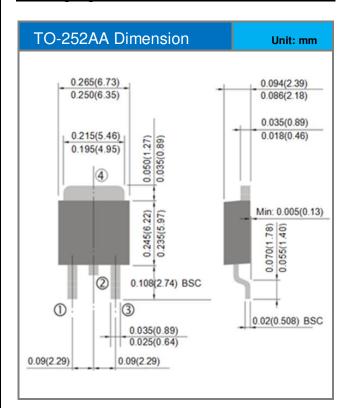


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width





Packaging Information



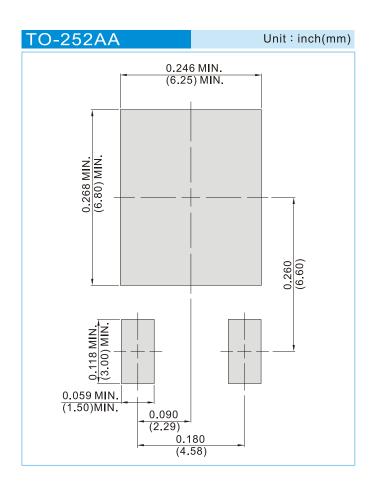




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJD30N15_L2_00001	TO-252AA	3,000pcs / 13" reel	D30N15	Halogen free	

MOUNTING PAD LAYOUT







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